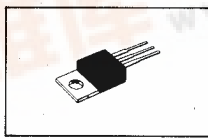




No.1309



**2SC3173**

NPN Epitaxial Planar Type Silicon Transistor  
FOR CRT HORIZONTAL DEFLECTION OUTPUT

Features:

- High switching speed
- Especially suited for use in high-definition CRT display ( $V_{CC}=6$  to  $12V$ )
- Wide ASO and durable against breakdown

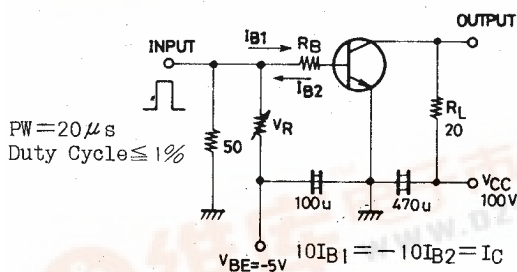
Absolute Maximum Ratings at  $T_a=25^\circ C$

			unit
Collector to Base Voltage	$V_{CBO}$	330	V
Collector to Emitter Voltage	$V_{CEO}$	150	V
Emitter to Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	7	A
Peak Collector Current	$i_{cp}$	12	A
Base Current	$I_B$	4	A
Collector Dissipation	$P_C$ $T_c=25^\circ C$	50	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ C$

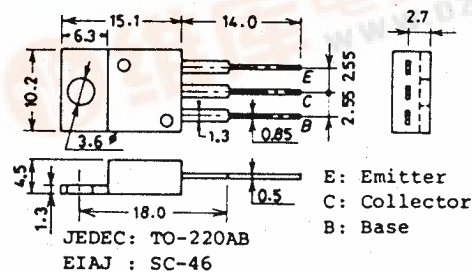
Electrical Characteristics at  $T_a=25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=200V, I_E=0$			100	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			100	$\mu A$
DC Current Gain	$h_{FE}(1)$	$V_{CE}=1V, I_C=1A$	15			
	$h_{FE}(2)$	$V_{CE}=1V, I_C=5A$	10	50		
Gain Bandwidth Product	$f_T$	$V_{CE}=10V, I_C=0.5A$	10	40		MHz
C-E Saturation Voltage	$V_{CE}(sat)$	$I_C=5A, I_B=0.5A$			1	V
B-E Saturation Voltage	$V_{BE}(sat)$	$I_C=5A, I_B=0.5A$			1.2	V
C-B Breakdown Voltage	$V(BR)_{CBO}$	$I_C=1mA, I_E=0$	330			V
C-E Breakdown Voltage	$V(BR)_{CEO}$	$I_C=1mA, R_{BE}=\infty$	150			V
E-B Breakdown Voltage	$V(BR)_{EBO}$	$I_E=1mA, I_C=0$	6			V
Fall Time	$t_f$	$I_C=5A, I_{B1}=-I_{B2}=0.5A$			0.5	$\mu s$

Switching Time Test Circuit



Case Outline 2010A  
(unit:mm)



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